

**IN THE CLAIMS:**

Please cancel claims 1-48, 53, 54 and 74 without prejudice or disclaimer, and amend claims 49, 58, 59, 75, 76, 78-83 and 87 as follows. This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

Claims 1-48 (Canceled).

Claim 49 (Currently Amended): A method of fabricating a thin film transistor substrate for a display device, comprising:

- a first step of forming a gate line on a substrate;
- a second step of forming a gate insulating film covering the gate line;
- a third step of forming a semiconductor layer at a desired area on the gate insulating film;
- a fourth step of forming a data line crossing the gate line, a source electrode connected to the data line and a drain electrode opposed to the source electrode on the gate insulating film;
- a fifth step of forming a protective film in such a manner to cover the gate line, the data line, the source electrode and the drain electrode; and
- a sixth step of forming a pixel electrode making an interface with the protective film at the remaining area excluding an area where the protective film is formed and connected to a side surface of the drain electrode;